

< C band internally matched power GaAs FET >

MGFC41V3642

3.6 – 4.2 GHz BAND / 14W

DESCRIPTION

The MGFC41V3642 is an internally impedance-matched GaAs power FET especially designed for use in 3.6 – 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

- High output power
P1dB=14W (TYP.) @f=3.6 – 4.2GHz
- High power gain
GLP=12.5dB (TYP.) @f=3.6 – 4.2GHz
- High power added efficiency
P.A.E.=40% (TYP.) @f=3.6 – 4.2GHz
- Low distortion [item -51]
IM3=-45dBc (TYP.) @Po=30dBm S.C.L

APPLICATION

- item 01 : 3.6 – 4.2 GHz band power amplifier
- item 51 : 3.6 – 4.2 GHz band digital radio communication

QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=3.4A • RG=50ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	12	A
IGR	Reverse gate current	-30	mA
IGF	Forward gate current	63	mA
PT *1	Total power dissipation	57.7	W
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

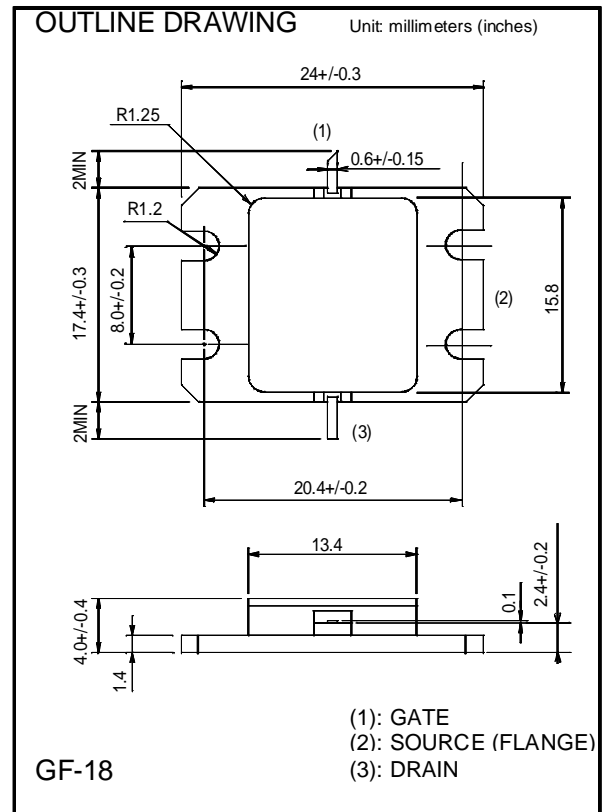
*1 : Tc=25°C

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	-	12	A	
gm	Transconductance	VDS=3V, ID=3.0A	-	3	-	S	
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=30mA	-	-	-5	V	
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=3.4A f=3.6 – 4.2GHz	40	41.5	-	dBm	
GLP	Linear Power Gain		11	12.5	-	dB	
ID	Drain current		-	3.3	-	A	
P.A.E.	Power added efficiency		-	40	-	%	
IM3 *2	3rd order IM distortion		-42	-45	-	dBc	
Rth(ch-c) *3	Thermal resistance		delta Vf method	-	-	2.8	°C/W

*2 : item -51 , 2 tone test, Po=30dBm Single Carrier Level , f=4.2GHz, delta f=10MHz

*3 : Channel-case



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